

PATENT APPLICATION
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q75721

Koichi TERASHIMA

Appln. No.: Unknown

Confirmation No.: Unknown

Group Art Unit: Unknown

Filed: August 21, 2003

Examiner: Unknown

For: SEMICONDUCTOR DEVICE AND SEMICONDUCTOR DEVICE
MANUFACTURING METHOD

INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. §§ 1.97 and 1.98

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

1. JP-A 2001-267413 published September 28, 2001.
2. JP-A 2002-110780 published April 12, 2002.
3. T. MIZUNO et al., "Advanced SOI p-MOSFETs with Strained-Si Channel on SiGe-on-Insulator Substrate Fabricated by SIMOX Technology," *IEEE Transactions on Electron Devices*, Vol. 48, No. 8, August 2001, pp. 1612-1618.
4. JP-A 2994227 published October 22, 1999.
5. JP-B2 3221901 published August 17, 2001.

One copy of each of the listed documents is submitted herewith.

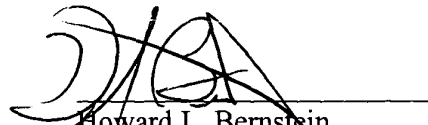
K. TERASHIMA
Q75721
Information Disclosure Statement

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date for an application other than a continued prosecution application (CPA) under §1.53(d); (2) Before the mailing date of the first Office Action on the merits (whichever is later); or (3) Before the mailing date of the first Office Action after filing a request for continued examination (RCE) under §1.114, and therefore, no Statement under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

In compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for foreign language documents, Applicant states that the references are discussed within the specification beginning at page 2, paragraphs 4-6.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

Respectfully submitted,


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WASHINGTON OFFICE
23373
CUSTOMER NUMBER

Date: August 21, 2003

Substitute for Form 1449 A & B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>	
				Application Number	Unknown
				Confirmation Number	Unknown
				Filing Date	August 21, 2003
				First Named Inventor	Koichi TERASHIMA
				Art Unit	Unknown
Examiner Name	Unknown				
Sheet	1	of	1	Attorney Docket Number	Q75721

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² <i>(if known)</i>		
		US			
		US			
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ <i>(if known)</i>			
		JP	2001-267413	A	09-28-2001		No
		JP	2002-110780	A	04-12-2002		No
		JP	2994227	A	10-22-1999		No
		JP	3221901	B2	08-17-2001		No

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
		T. MIZUNO et al., "Advanced SOI p-MOSFETs with Strained-Si Channel on SiGe-on-Insulator Substrate Fabricated by SIMOX Technology," <i>IEEE Transactions on Electron Devices</i> , Vol. 48, No. 8, August 2001, pp. 1612-1618	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to indicate here if English language Translation is attached.